

FORM PTO-892 (REV. 2-92)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		SERIAL NO. 09-683863		GROUP/ART UNIT 2817		ATTACHMENT TO PAPER NUMBER 13				
NOTICE OF REFERENCES CITED				APPLICANT(S) McGrath								
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•		DOCUMENT NO.				DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE		
	A	6344663				25-2002	Slater, Jr et al.	257	72			
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	T	Schmid et al. "Process technology and high temperature performance of 6H-SiC MOS devices" The Third European Conference on High temperature Electronics 1999 pp 195-199										
EXAMINER		DATE										
MICHAEL B SHINGLETON		4-3-03										
* A copy of this reference is not being furnished with this office action. (See Manual of Patent Examining Procedure, section 707.05 (a).)												